

### A1: LIST OF SCIENTIFIC (PEER REVIEWED) PUBLICATIONS

NO.	Title	Main author	Title of the periodical or the series	Number, date or frequency	Publisher	Place of publication	Year of publication	Relevant pages	Permanent identifiers <sup>1</sup> (if available)	Is/Will open access <sup>2</sup> provided to this publication?
<b>IEE</b>										
1	Ni/Au-Al <sub>2</sub> O <sub>3</sub> gate stack prepared by low-temperature ALD and lift-off for MOSHEMTs.	Blaho, M.,	Microelectronics Engineering	Vol. 112, March 2013	Elsevier	Holland	2013	204-207		no
2	Adjustment of threshold voltage in AlN/AlGa <sub>N</sub> /Ga <sub>N</sub> high-electron mobility transistors by plasma oxidation and Al <sub>2</sub> O <sub>3</sub> atomic layer deposition overgrowth	Gregušová, D.	Applied Phys. Letters	Vol. 104, January 2014	American Institute of Physics	USA	2014	013506-1-4		no
3	Degradation of Al-GaN/GaN high-electron mobility transistors in the current-controlled off-state breakdown	Kuzmik, J.	J. Applied Physics	Vol. 115, April 2014	American Institute of Physics	USA	2014	164504-1-4		no

<sup>1</sup> A permanent identifier should be a persistent link to the published version full text if open access or abstract if article is pay per view) or to the final manuscript accepted for publication (link to article in repository).

<sup>2</sup> Open Access is defined as free of charge access for anyone via Internet. Please answer "yes" if the open access to the publication is already established and also if the embargo period for open access is not yet over but you intend to establish open access afterwards.

4	Self-heating in GaN transistors designed for high-power operation	Kuzmik, J.	IEEE Trans. Electron Devices	Vol. 61, No. 10, October 2014	Institute of Electrical and Electronics Engineers	USA	2014	3429-3434		
5	A comprehensive analytical model for threshold voltage calculation in GaN based metal-oxide-semiconductor high-electron-mobility transistors	Tapajna, M.	Applied Phys. Letters	Vol. 100, March 2012	American Institute of Physics	USA	2012	113509-1-4		no
6	Impact of GaN cap on charges in Al <sub>2</sub> O <sub>3</sub> /(GaN)/AlGaIn/GaN metal-oxide-semiconductor heterostructures analyzed by means of capacitance measurements and simulations	Tapajna, M.	J. Applied Physics	Vol. 116, September 2014	American Institute of Physics	USA	2014	104501-1-7		no
7	Bulk and interface trapping in the gate dielectric of GaN based metal-oxide-semiconductor high-electron-mobility transistors	Tapajna, M.	Applied Phys. Letters	Vol. 102, June 2013	American Institute of Physics	USA	2013	243509-1-4		no
8	Control of Threshold Voltage in GaN Based Metal–Oxide–Semiconductor High-Electron Mobility Transistors towards the Normally-Off Operation	Tapajna, M.	Japanese J. Applied Physics	Vol. 52, May 2013	The Japan Society of Applied Physics	Japan	2013	08JN08-1-5		no

UniPd										
9	Random telegraph signal noise in gate current of unstressed and reverse-bias-stressed AlGaN/GaN high electron mobility transistors	Marko, P.	Applied Physics Letters	Vol. 100	AIP	USA	2012	143507		no
10	Breakdown mechanisms in AlGaN/GaN HEMTs: An overview	Meneghesso, G.	Japanese Journal of Applied Physics	Vol. 53		Japan	2014	100211		no
11	Single- and double-heterostructure GaN-HEMTs devices for power switching applications	Zanandrea, A.	Microelectronics Reliability	Vol. 52, no. 9-10	Elsevier	UK	2012	2426–2430		no
TU Vienna										
12	Fixed interface charges between AlGaN barrier and gate stack composed of in situ grown SiN and Al <sub>2</sub> O <sub>3</sub> in Al-GaN/GaN high electron mobility transistors with normally off capability”	Capriotti, M.	Appl. Phys. Lett.	Vol. 104			2014	113502		no
13	Statistics and localization of vertical breakdown in Al-GaN/GaN HEMTs on SiC and Si substrates for power applications	Fleury, C.	Microelectronics Reliability	Vol. 53, no. 9-11	Elsevier	UK	2013	1444-1449		no

FBH										
14	Fast GaN based Schottky di-odes on Si(111) substrate with low onset voltage and strong reverse blocking	Bahat-Treidel, E.	Phys. stat. sol. (c),	Vol. 10, no. 5			2013	pp. 849-852		no
15	Impact of Buffer Composition on the Dynamic On-State Resitance of High-Voltage AlGaIn/GaN HFETs	Hilt, O.	24th Int. Symp. On Power Semiconductor Devices and Ics (ISPSD)				2012	pp. 345-348		
16	Improved Vertical Isolation for Normally-off High Voltage GaN-HFETs on n-SiC Substrates	Hilt, O.	IEEE Transactions on Electron Devices	Vol. 60, no. 10			2013	pp. 3084-3090		no
17	Normally-off GaN Transistors for Power Applications	Hilt, O.	ECS Transactions	Vol. 58 (4)			2013	pp. 145-154		no
18	Normally-off GaN Transistors for Power Applications	Hilt, O.	J. Phys.: Conf. Ser	Vol. 494			2014	012001		no
19	Vertical Blocking Voltage Improvement of GaN HEMT Structures on n-SiC by Pre-Epitaxial Substrate Implantation	Kotara, P.	ECS J. Solid State Sci. Technol.	Vol. 2, no. 8			2013	pp. N3064-N3067		no
20	Single Image Spectral Electroluminescence (Photon Emission) of GaN HEMTs	Scholz, P.	IEEE Int. Reliab. Phys. Symp.				2013	pp. CD.3.1-CD.3.7.		no

			(IRPS)							
21	Device breakdown and dynamic effects in GaN power switching devices: Dependencies on material properties and device design	Würfl, J.	ECS Meeting Abstracts MA2012-02, Pacific RIM Meeting (PRiME 2012)				2012			no
22	Device breakdown and dynamic effects in GaN power switching devices: Dependencies on material properties and device design	Würfl, J.	ECS Transactions	Vol. 50, No. 3			2012	pp. 211-222		no
23	Technological approaches towards high voltage, fast switching GaN power transistors	Würfl, J.	ECS Trans.	Vol. 52, no. 1			2013	979-989		no
24	Enabling GaN High Speed Devices: Microwave Meets Power Electronics - and vice versa	Würfl, J.	Proc. 8th European Microwave Integrated Circuits Conf. (EuMIC 2013)				2013	pp. 176-179		no

25	Techniques towards GaN power transistors with improved high voltage dynamic switching properties	Würfl, J.	IEEE 2013 International Electron Devices Meeting (IEDM), Washington, DC, USA				2013	pp. 6.1.1 - 6.1.4		no
<b>AIXTRON</b>										
26	HCl-assisted-growth of GaN and AlN	Fahle, D.	Journal of Crystal Growth	370	Elsevier	Netherlands	2013	30-35		no